

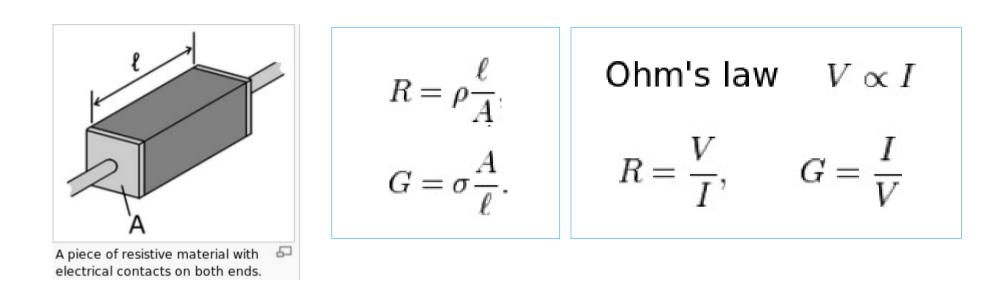
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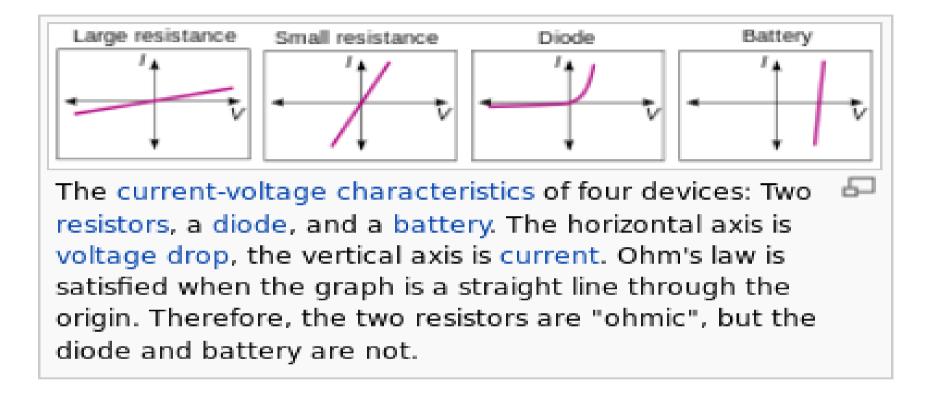
Resistance



the derivative $rac{dV}{dI}$ may be most useful; this is called the "differential resistance".

$$I_{d} = k' \frac{W}{L} \left[\left(v_{gs} - v_{t} \right) v_{ds} - \frac{1}{2} v_{ds}^{2} \right]$$

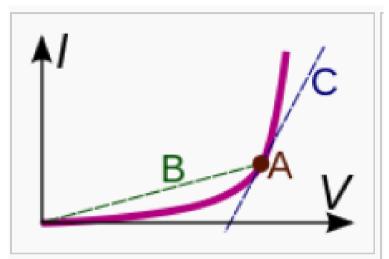
I-V Characteristics



Slope

the derivative $\displaystyle rac{dV}{dI}$ may be most useful; this is called the "differential resistance".

Static & Derivative Resistance



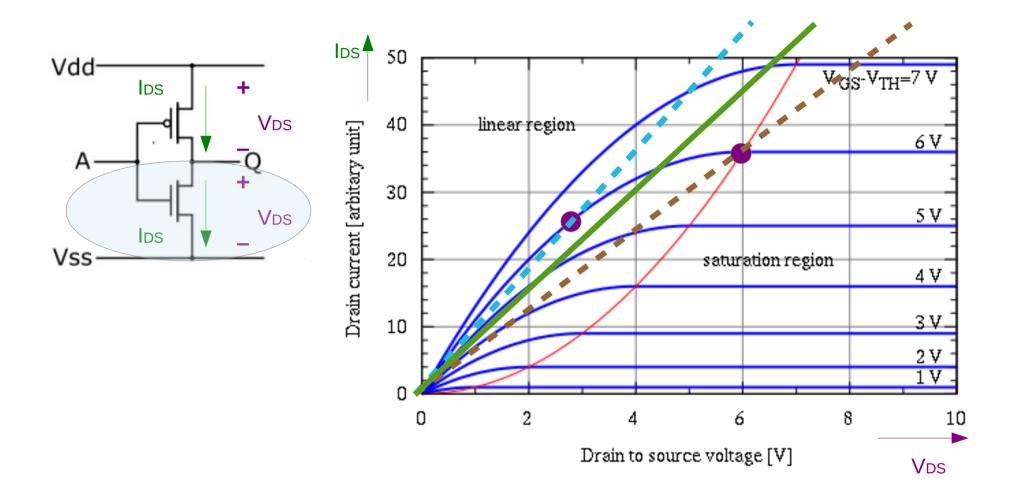
The IV curve of a non-ohmic device (purple). Point A represents the current and voltage values right now. The **static resistance** is the **inverse slope** of line B through the origin. The **differential resistance** is the inverse slope of tangent line C. Static resistance (also called chordal or DC resistance) - This corresponds to the usual definition of resistance; the voltage divided by the current

$$R_{\text{static}} = \frac{v}{i}$$
.

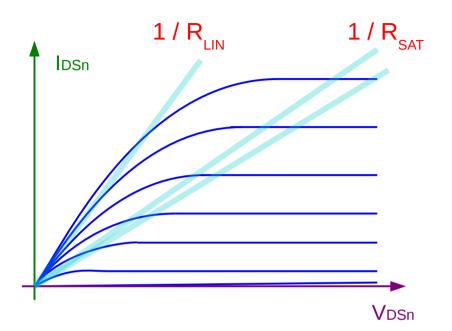
 Differential resistance (also called dynamic, incremental or small signal resistance) Differential resistance is the derivative of the voltage with respect to the current; the slope of the IV curve at a point

$$R_{\text{diff}} = \frac{dv}{di}$$

nMOS Resistance



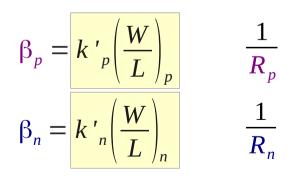
Transconductance Parameters



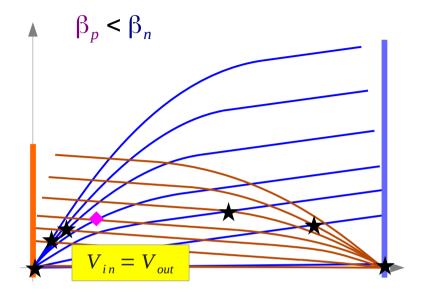
When
$$V_{GS} > V_t$$
 and $V_{DS} < (V_{GS} - V_t)$
$$I_d = \frac{k' \frac{W}{L}}{\left[(v_{gs} - v_t) v_{ds} - \frac{1}{2} v_{ds}^2 \right]}$$

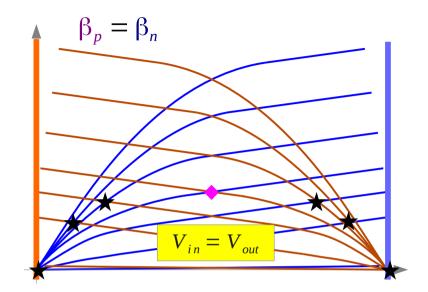
When
$$V_{GS} > V_{t}$$
 and $V_{DS} \ge (V_{GS} - V_{t})$

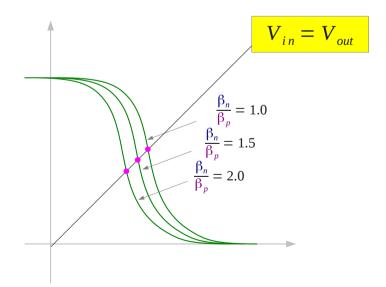
$$I_d = \frac{1}{2} \frac{k' \frac{W}{L}}{L} (v_{gs} - v_t)^2$$



Transconductance and Characteristic Curves





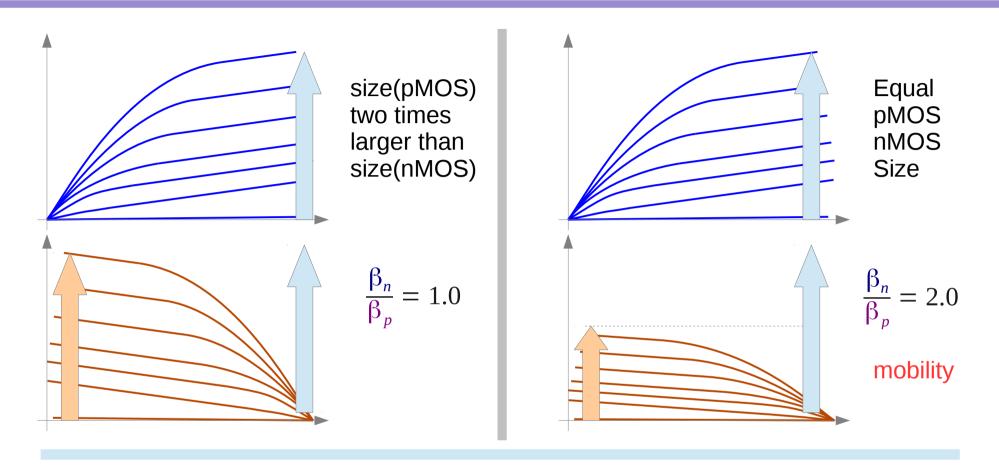


$$\beta_n > \beta_p \qquad \left(\frac{\beta_n}{\beta_p} > 1\right)$$

nMOS more easily turns on

 $\rm V_{_{out}}$ easily becomes L, for a smaller $\rm V_{_{in}}$

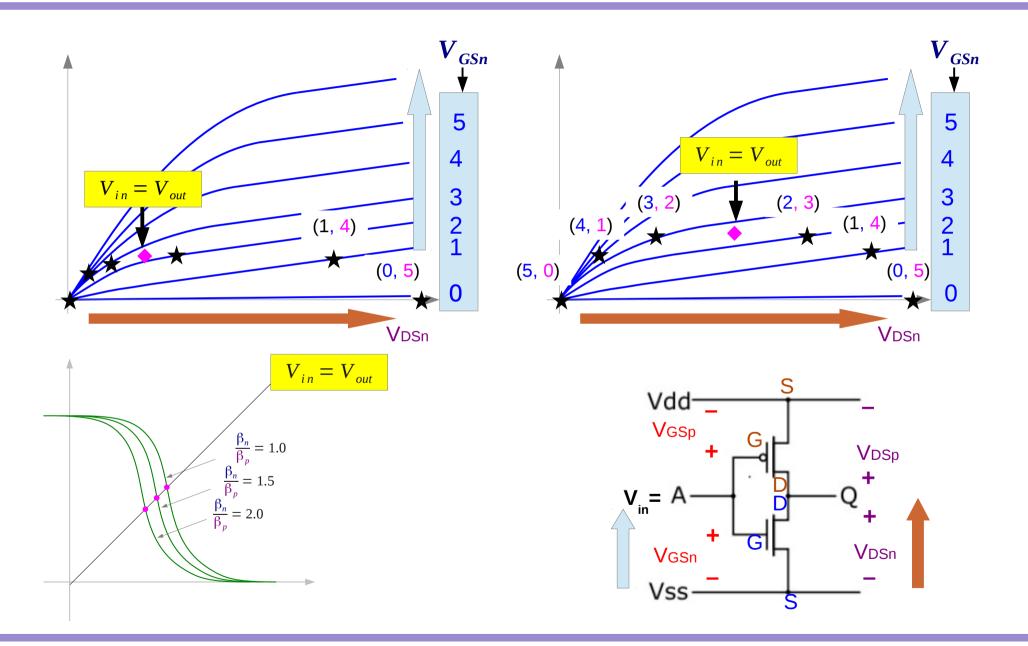
Transconductance and Transistor Size



When
$$V_{GS} > V_t$$
 and $V_{DS} < (V_{GS} - V_t)$
$$I_d = \beta \left[(v_{gs} - v_t) v_{ds} - \frac{1}{2} v_{ds}^2 \right]$$

When
$$V_{GS} > V_t$$
 and $V_{DS} \ge (V_{GS} - V_t)$
$$I_d = \frac{1}{2} \beta (v_{gs} - v_t)^2$$

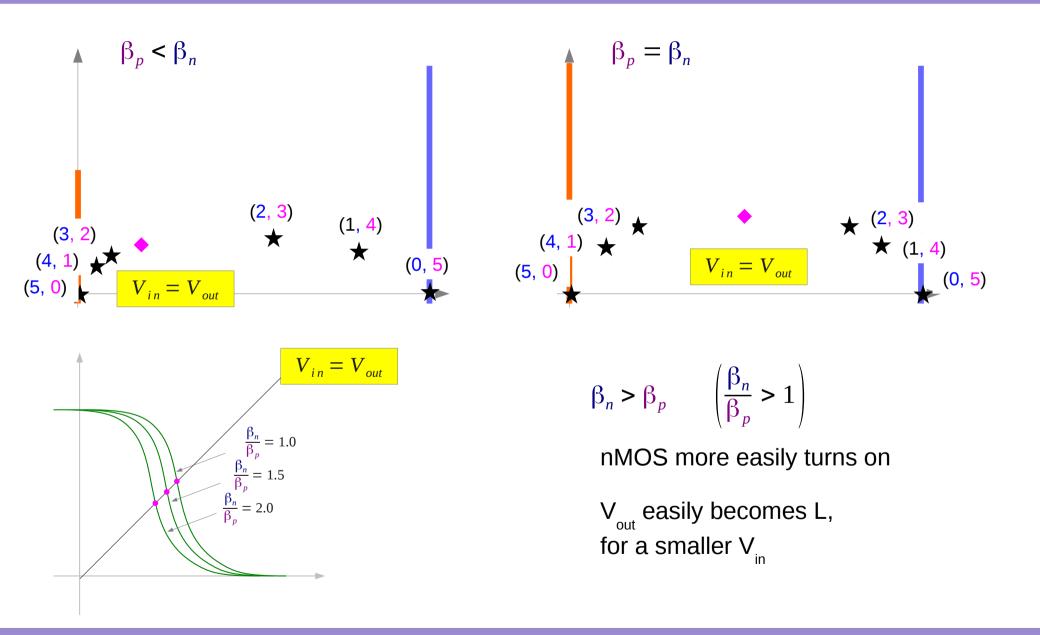
Transconductance and Switching



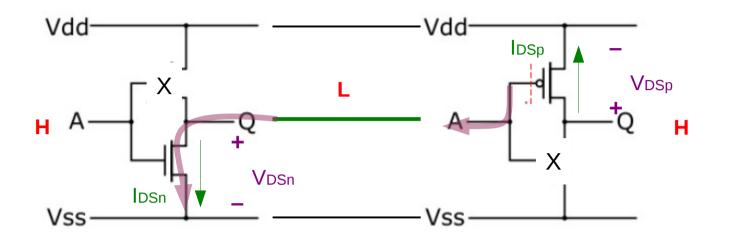
Device R, C (2E)

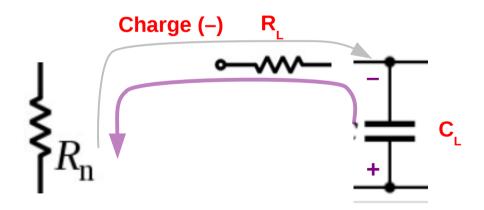
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Transconductance and Characteristic Curves

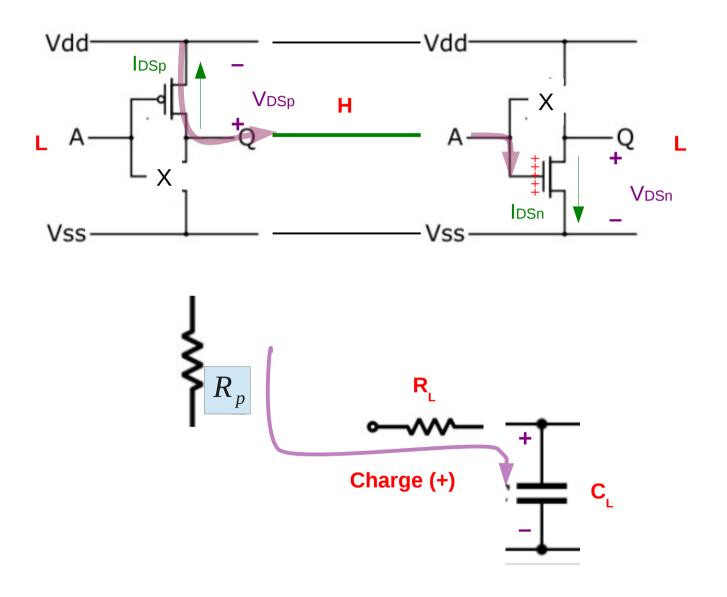


Resistance (5)

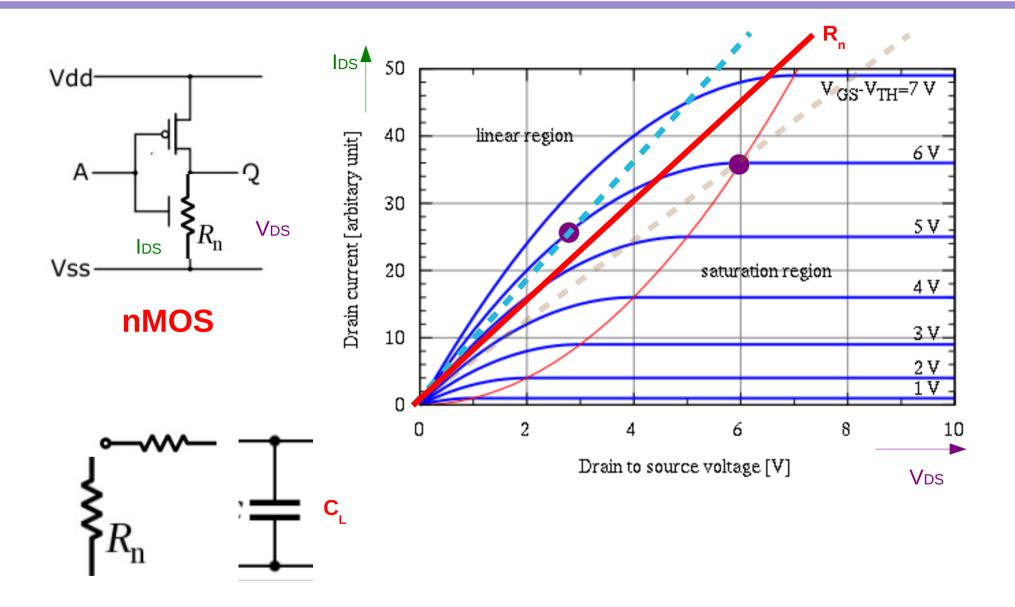




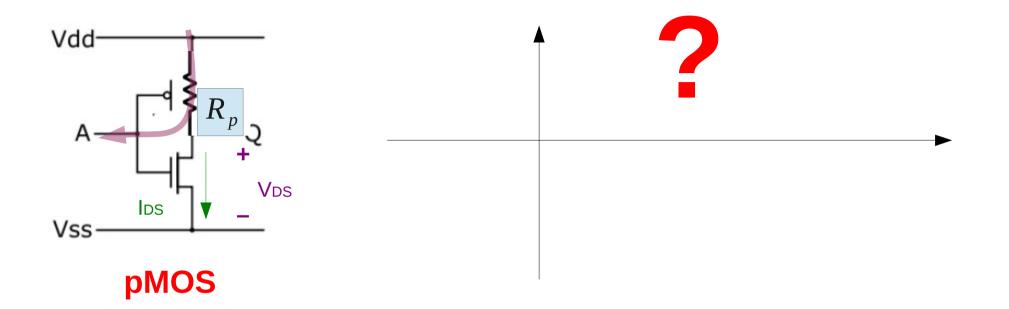
Resistance (6)

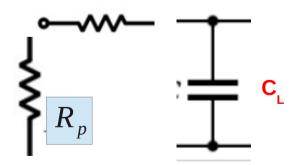


Resistance (6)

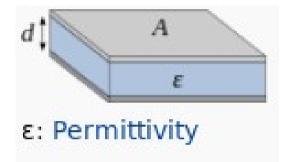


Resistance (7)

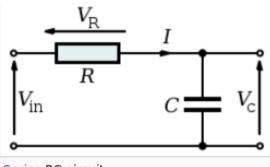












Series RC circuit

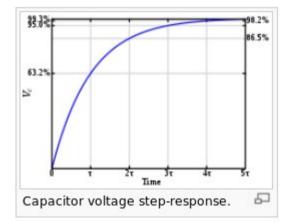
By viewing the circuit as a voltage divider, the voltage across the capacitor is:

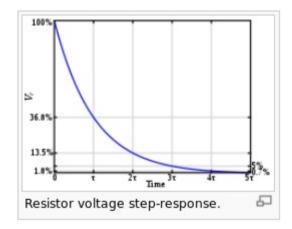
$$V_C(s) = \frac{1/Cs}{R + 1/Cs} V_{in}(s) = \frac{1}{1 + RCs} V_{in}(s)$$

and the voltage across the resistor is:

$$V_R(s) = \frac{R}{R+1/Cs} V_{in}(s) = \frac{RCs}{1+RCs} V_{in}(s)$$

$$V_C(t) = V \left(1 - e^{-t/RC} \right)$$
$$V_R(t) = V e^{-t/RC}.$$





Time Constant

Device R, C (2E)

Thus, the voltage across the capacitor tends towards V as time passes, while the voltage across the resistor tends towards 0, as shown in the figures. This is in keeping with the intuitive point that the capacitor will be charging from the supply voltage as time passes, and will eventually be fully charged.

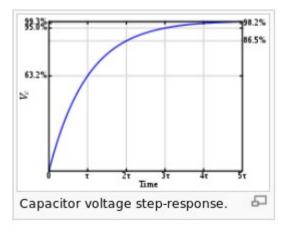
These equations show that a series RC circuit has a time constant, usually denoted $\tau = RC$ being the time it takes the voltage across the component to either rise (across C) or fall (across R) to within 1/e of its final value. That is, τ is the time it takes V_C to reach V(1 - 1/e) and V_R to reach V(1/e).

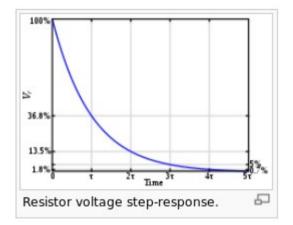
The rate of change is a $\mathit{fractional}\left(1-rac{1}{e}
ight)$ per au. Thus, in going from

t=N au to t=(N+1) au , the voltage will have moved about 63.2% of

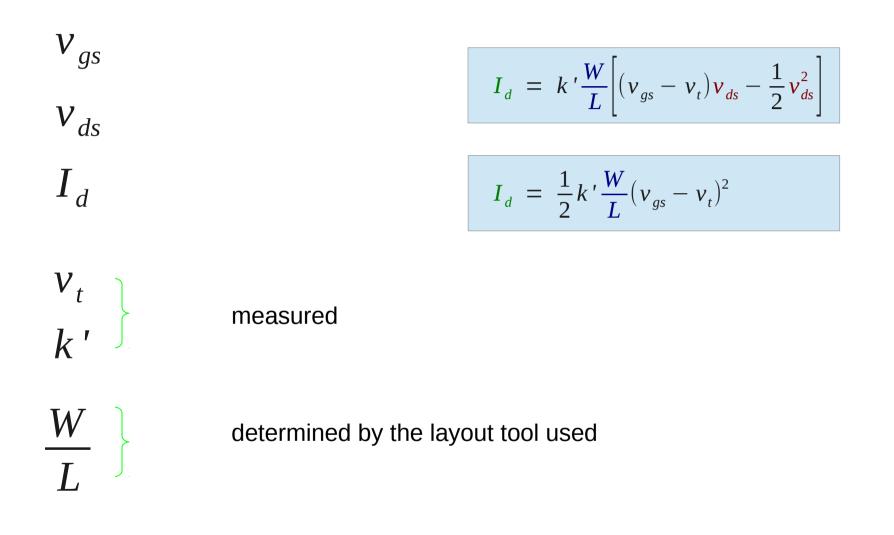
the way from its level at $t = N_T$ toward its final value. So C will be charged to about 63.2% after τ , and essentially fully charged (99.3%) after about 5_T . When the voltage source is replaced with a short-circuit, with C fully charged, the voltage across C drops exponentially with t from V towards 0. C will be discharged to about 36.8% after τ , and essentially fully discharged (0.7%) after about 5_T . Note that the current, I, in the circuit behaves as the voltage across R does, via Ohm's Law.

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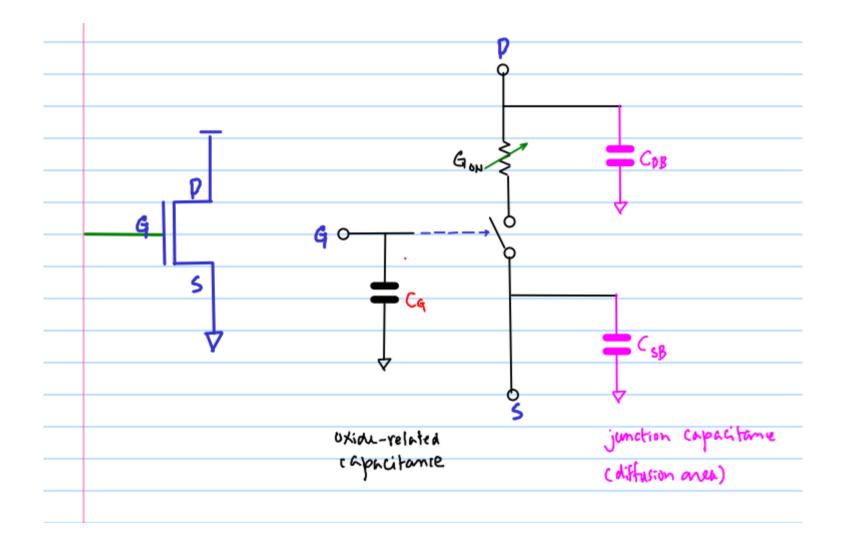




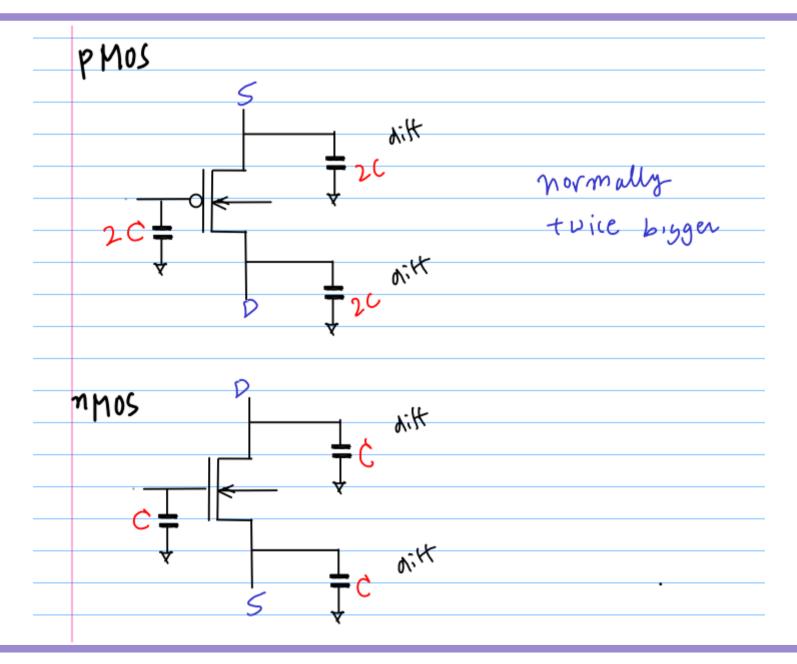
Simple Model



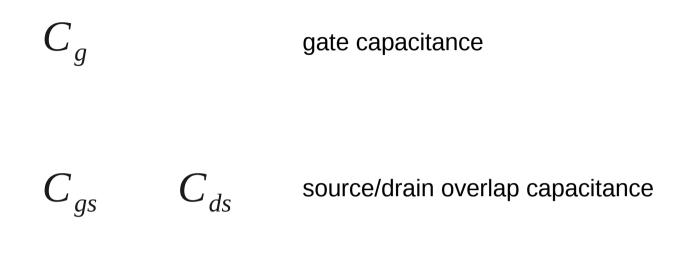
Simple Model



Transistor Parasitics



Transistor Parasitics





Wire Parasitics

wires vias transistors



Spice Model

wires vias transistors



Design Rule

wires vias transistors



References

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